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SEMICONDUCTOR



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GDT



PLED

PMEG2010AEH-MS

Product specification

Surface Mount Schottky Barrier Rectifier

Reverse Voltage - 20V

Forward Current -1.0 A

FEATURE

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SOD-123FL
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight:15mg 0.00048oz

Reference News

SOD-123FL	Pin Configuration	MARKING
		

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

Absolute Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase , half wave , 60Hz resistive or inductive load, for capacitive load , derate by 20 %

Parameter	Symbols	PMEG2010AEH-MS	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	V
Maximum RMS voltage	V_{RMS}	14	V
Maximum DC Blocking Voltage	V_{DC}	20	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1.0	A
Peak Forward Surge Current ,8 .3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30	A
Max Instantaneous Forward Voltage at 1 A	V_F	0.55	V
Maximum DC Reverse Current $T_a = 25^{\circ}C$ at Rated DC Reverse Voltage $T_a = 100^{\circ}C$	I_R	0.3 10	mA
Typical Junction Capacitance (1)	C_j	110	pF
Typical Thermal Resistance (2)	$R_{\theta JA}$	100	$^{\circ}C/W$
Operating Junction Temperature Range	T_j	-55 ~ +125	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 ~ +150	$^{\circ}C$

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B . mounted with 2 .0" X 2 .0" (5 X 5 cm) copper pad areas .

ELECTRICAL CHARACTERISTICS CURVE

Fig.1 Forward Current Derating Curve

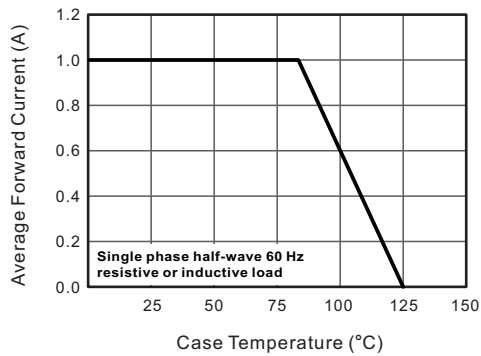


Fig.2 Typical Reverse Characteristics

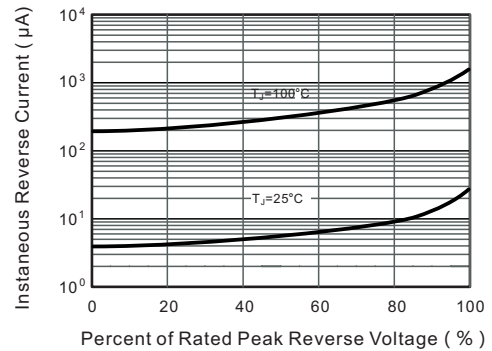


Fig.3 Typical Forward Characteristic

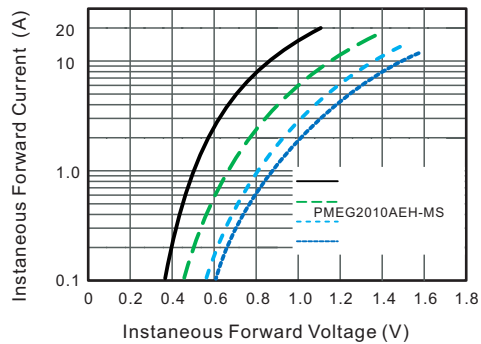


Fig.4 Typical Junction Capacitance

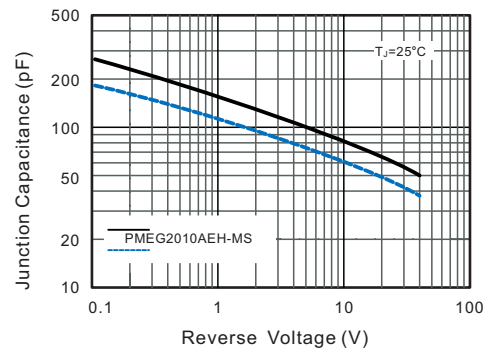


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

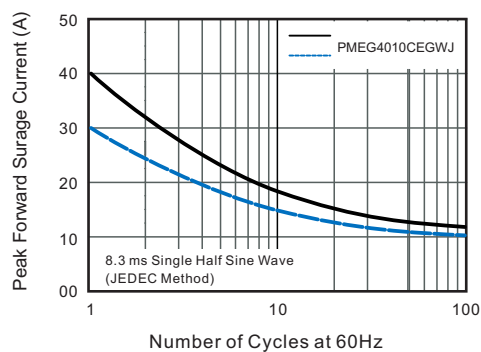
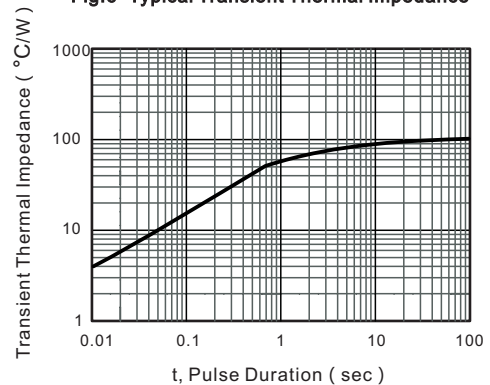
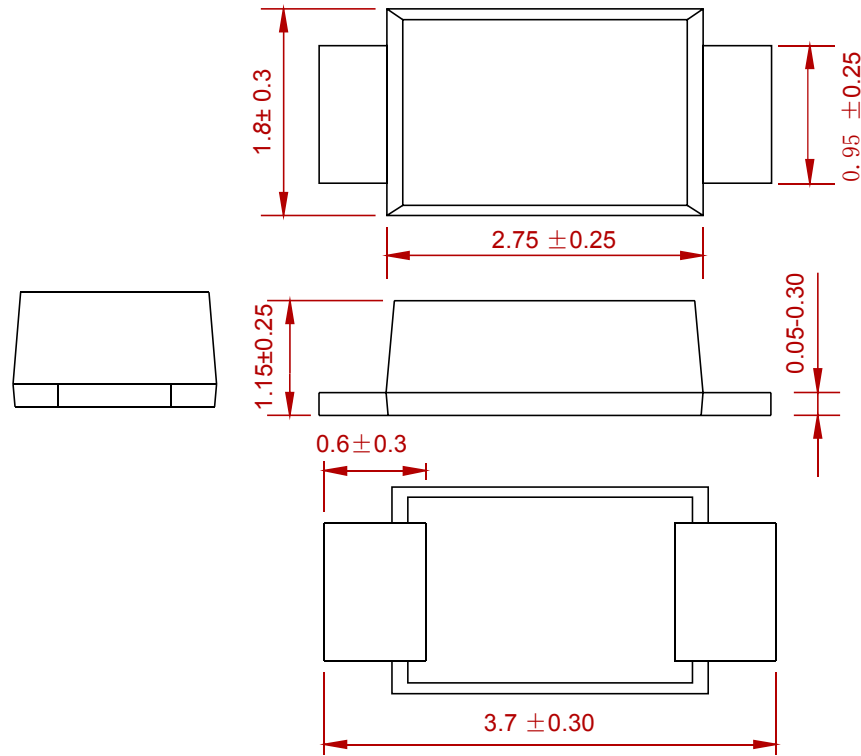


Fig.6- Typical Transient Thermal Impedance

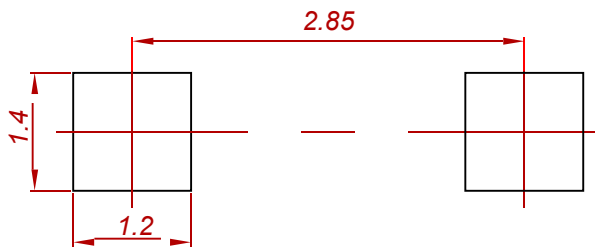


PACKAGE MECHANICAL DATA



Dimensions in millimeters

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PMEG2010AEH-MS	SOD-123FL	3000

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